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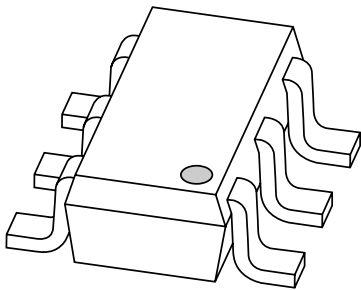
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DATA SHEET



**PBSS4140DPN**  
40 V low  $V_{CEsat}$  NPN/PNP  
transistor

# 40 V low $V_{CEsat}$ NPN/PNP transistor

# PBSS4140DPN

### FEATURES

- 600 mW total power dissipation
- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Replaces two SOT23 packaged low  $V_{CEsat}$  transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

### DESCRIPTION

NPN/PNP low  $V_{CEsat}$  transistor pair in an SC-74 (SOT457) plastic package.

### MARKING

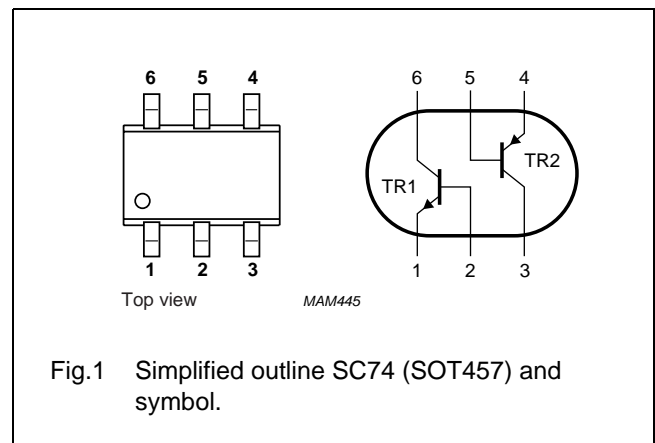
TYPE NUMBER	MARKING CODE
PBSS4140DPN	M2

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	40	V
$I_C$	peak collector current	1	A
$I_{CM}$	peak collector current	2	A
TR1	NPN	–	–
TR2	PNP	–	–
$R_{CEsat}$	equivalent on-resistance	<500	m $\Omega$

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



40 V low  $V_{CEsat}$  NPN/PNP transistor

## PBSS4140DPN

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	40	V
$V_{CEO}$	collector-emitter voltage	open base	–	40	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC)		–	1	A
$I_{CM}$	peak collector current		–	2	A
$I_{BM}$	peak base current		–	1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	370	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	600	mW

**Note**

1. Device mounted on a printed-circuit board, single side copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	208	K/W

**Note**

1. Device mounted on a printed-circuit board, single side copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

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## PBSS4140DPN

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

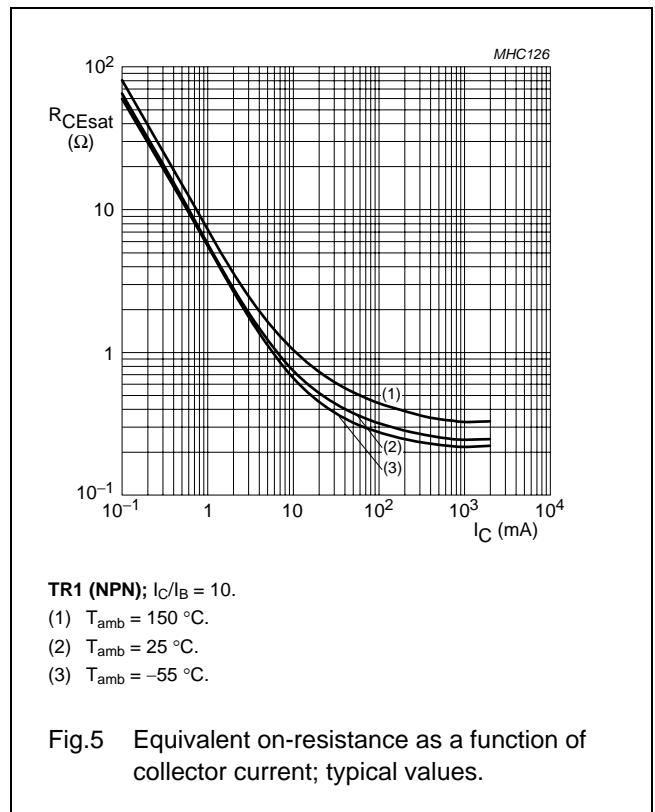
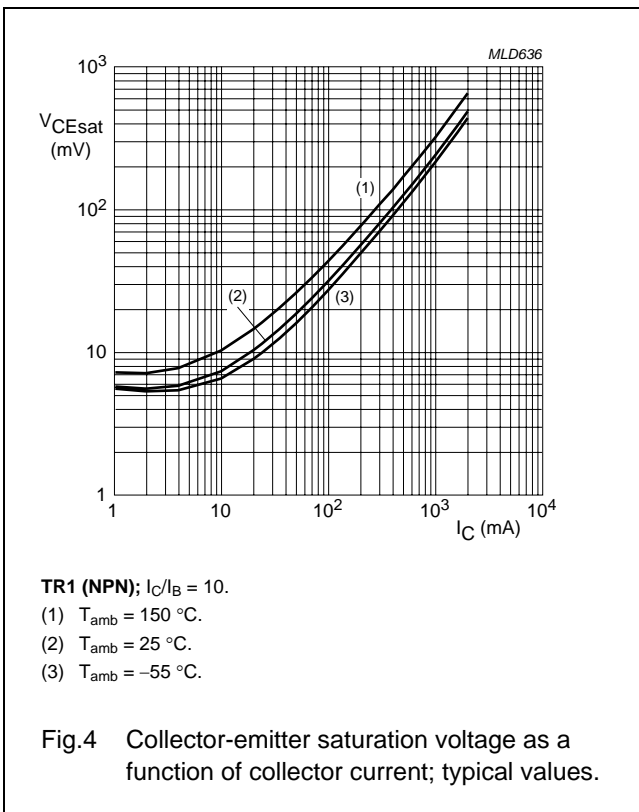
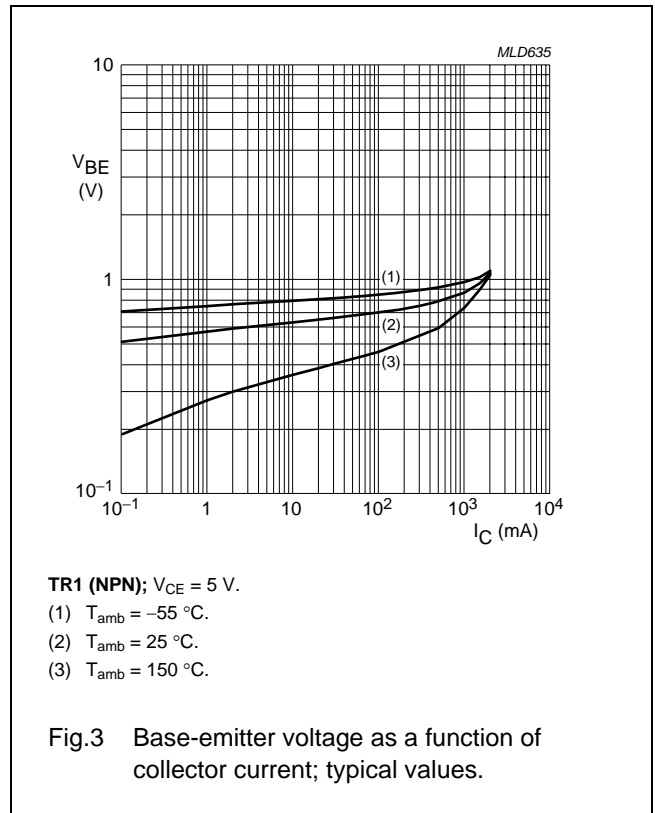
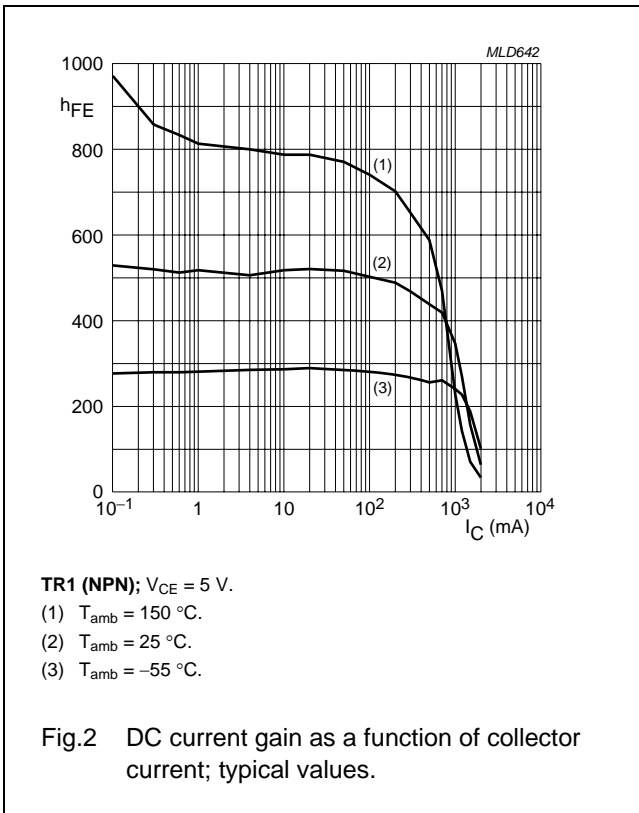
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor unless otherwise specified; for the PNP transistor with negative polarity</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 40\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0$	–	–	100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	300	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	–	200	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	–	250	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	500	mV
<b>NPN transistor</b>						
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	300	–	900	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	200	–	–	
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	–	–	1.1	V
$R_{CEsat}$	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	260	<500	$\text{m}\Omega$
$f_T$	transition frequency	$V_{CE} = 10\text{ V}; I_C = 50\text{ mA}; f = 100\text{ MHz}$	150	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	10	pF
<b>PNP transistor</b>						
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}$	300	–	800	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	250	–	–	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	160	–	–	
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	-1.0	V
$R_{CEsat}$	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	300	<500	$\text{m}\Omega$
$f_T$	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	150	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	12	pF

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

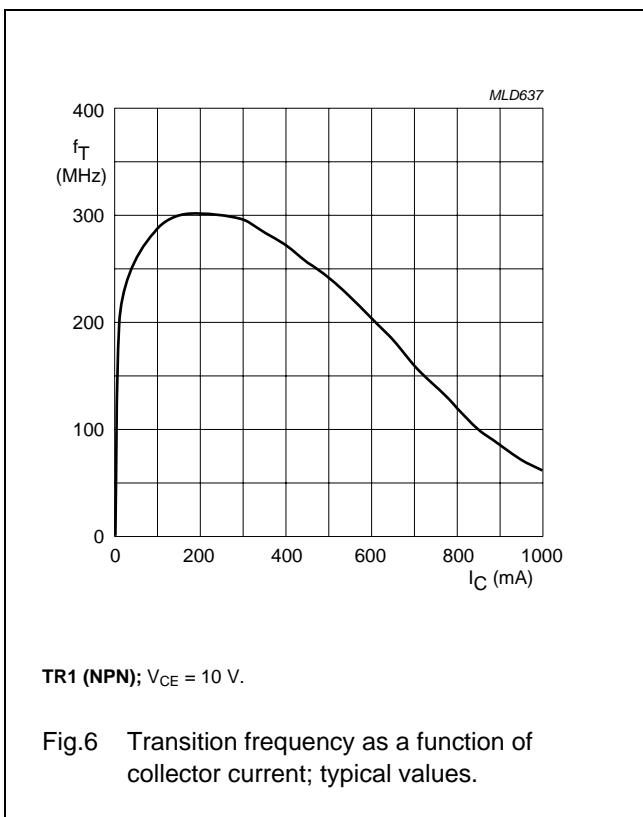
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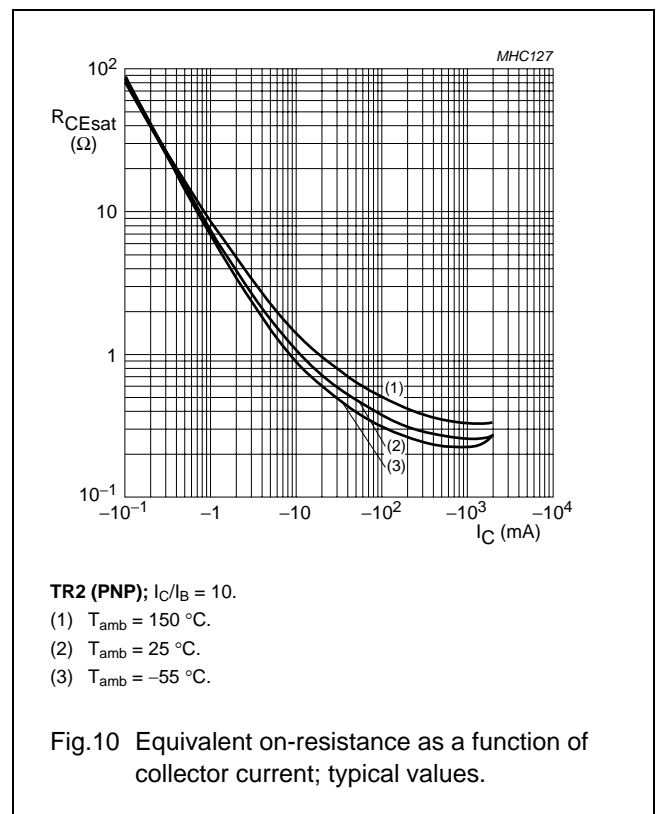
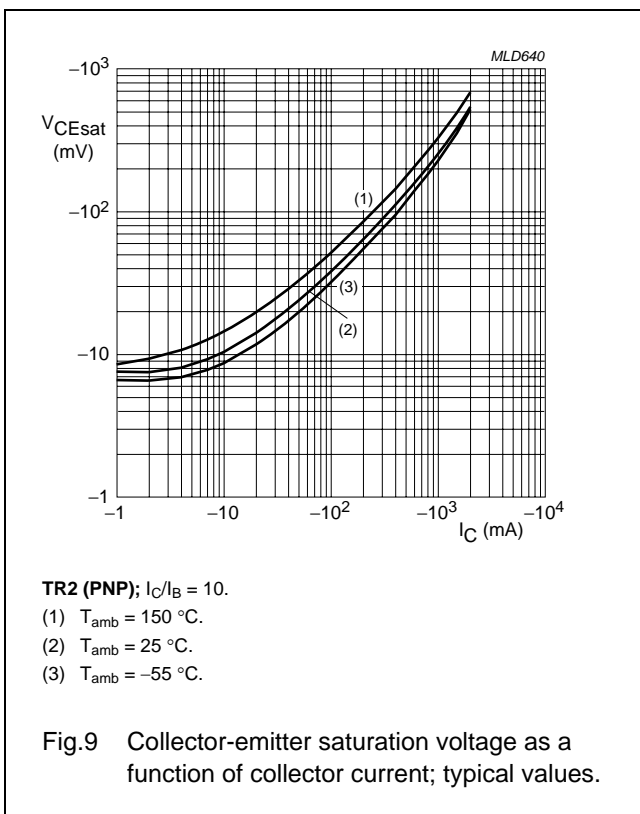
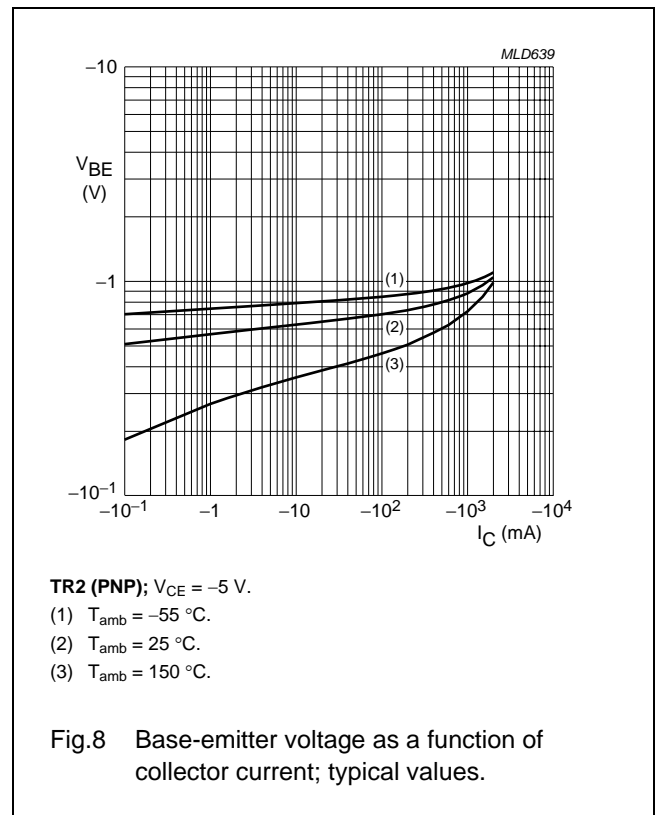
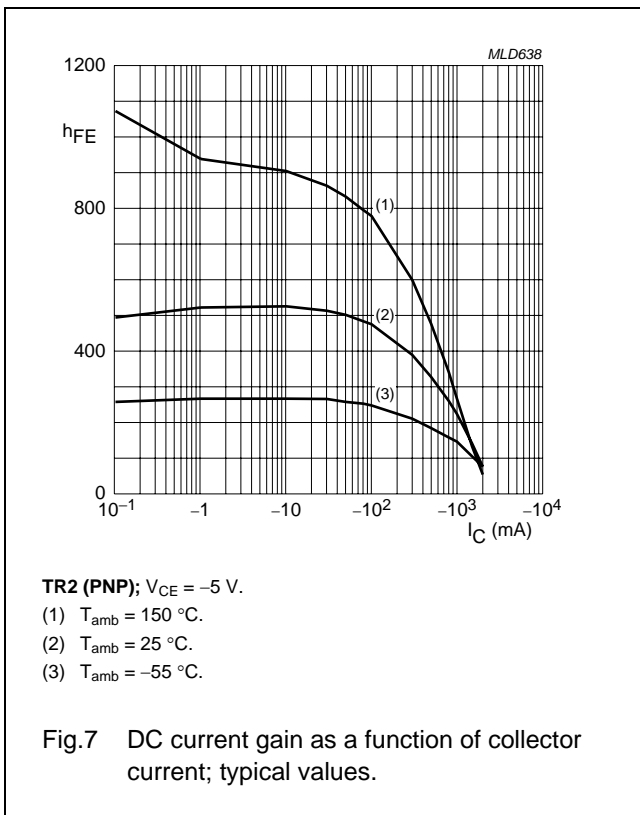
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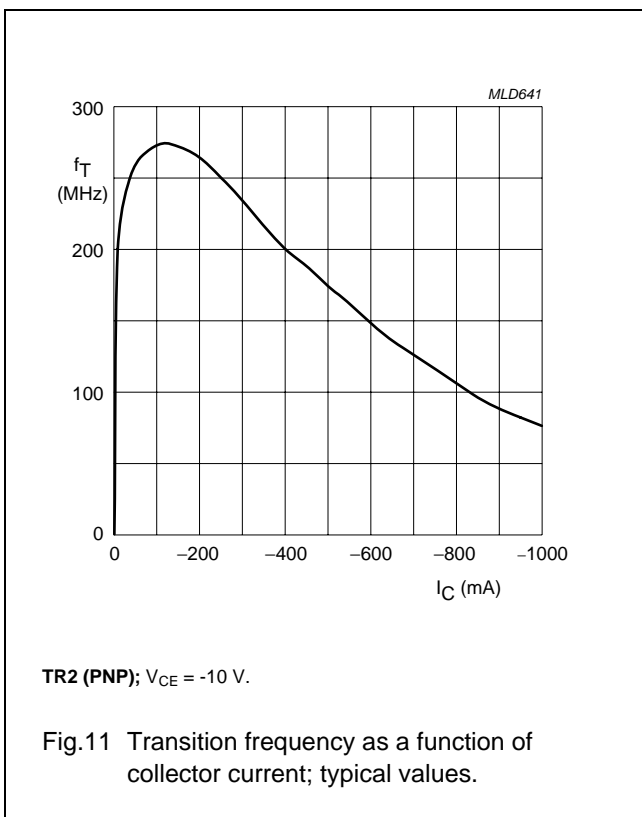
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40 V low  $V_{CEsat}$  NPN/PNP transistor

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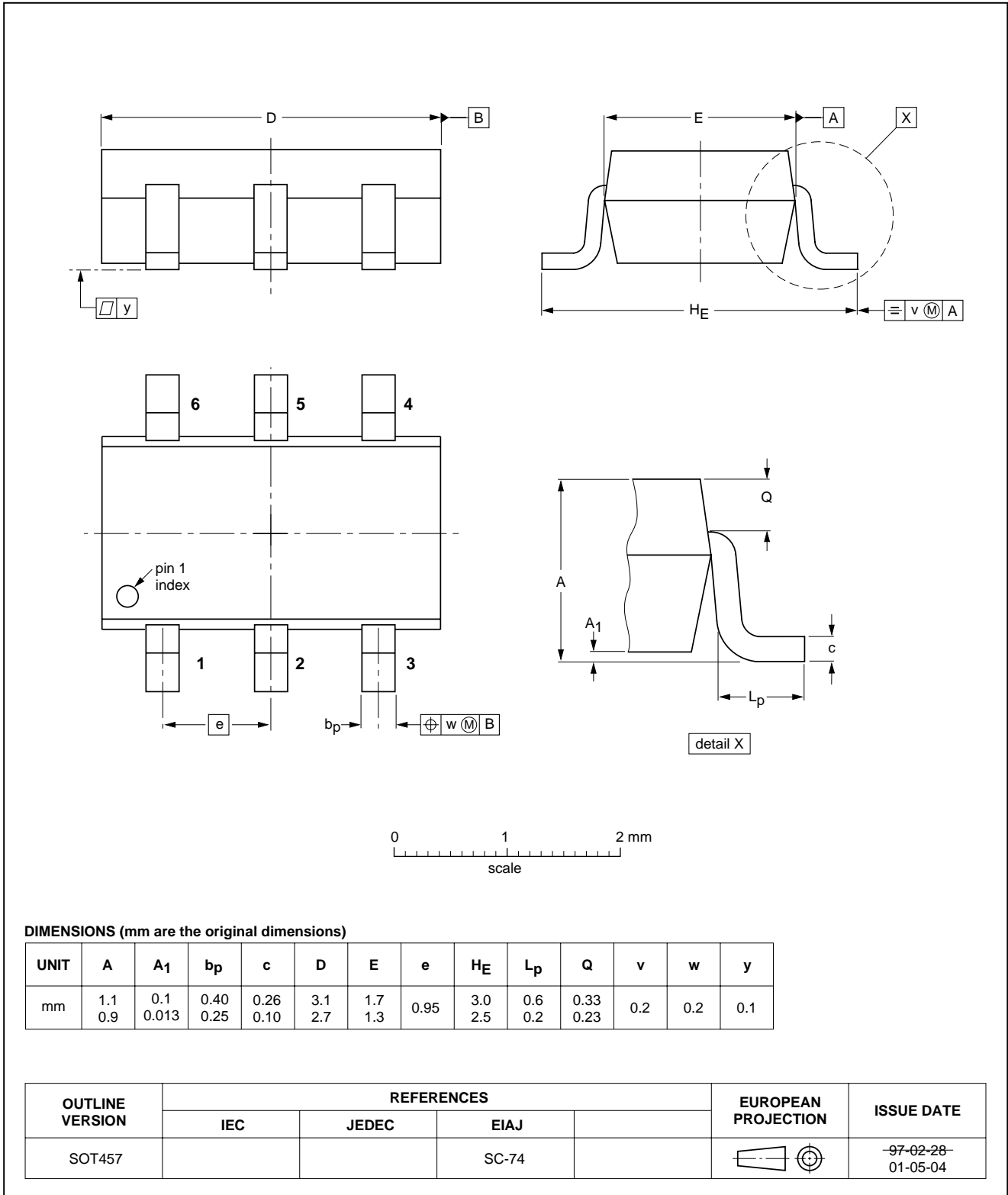
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



40 V low  $V_{CEsat}$  NPN/PNP transistor

PBSS4140DPN

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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# ***NXP Semiconductors***

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## **Contact information**

For additional information please visit: **<http://www.nxp.com>**

For sales offices addresses send e-mail to: **[salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)**

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